Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO247 plastic package.





2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			650		V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 109$ °C; Fig. 1; Fig. 2; Fig. 3		30			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 109 °C; square-wave pulse		60			Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270 297		Α	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	20	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		1/ 1/4 A
2	А	anode		K A 001aaa020
mb	mb	mounting base; connected to cathod	K A TO247-2L	

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity		Package issue date
BYC30MW-650PT2	TO247-2L	BYC30MW-650PT2Q	Tube	30	TO247L-2L	10-Nov-2020

7. Marking

Table 4. Marking codes

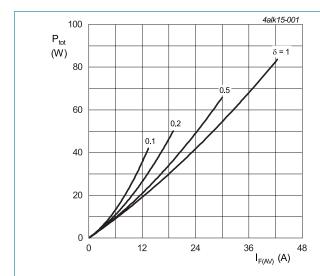
Type number	Marking codes
BYC30MW-650PT2	BYC30MW
	650PT2

8. Limiting values

Table 5. Limiting values

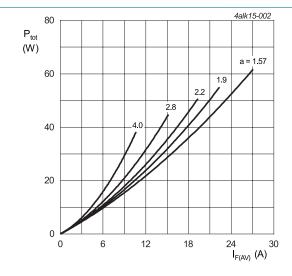
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 109$ °C; Fig. 1; Fig. 2; Fig. 3		30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 109 °C; square-wave pulse		60	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	Α
T _{stg}	storage temperature			-65 to 175	°C
T _j	junction temperature			-65 to 175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.436 \text{ V; R}_s = 0.0127 \Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.436 V; R_s = 0.0127 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

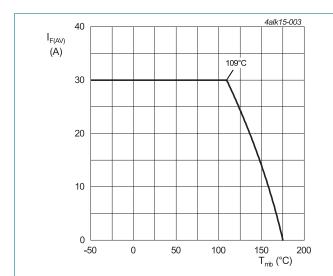


Fig. 3. Forward current as a function of mounting base temperature; maximum values

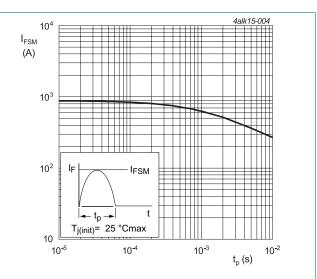


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	45	-	K/W

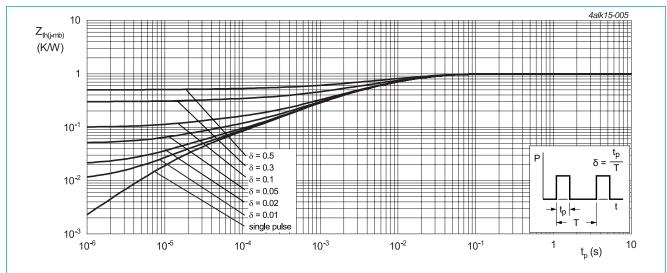


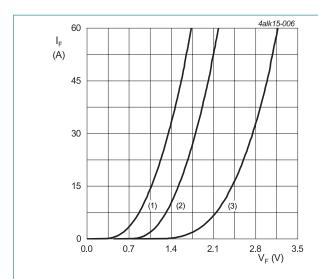
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						_
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.6	30	μΑ
		V _R = 650 V; T _j = 150 °C		-	0.25	1	mA
Dynamic	characteristics						
Q _r	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	68	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	330	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	20	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	38	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	73	-	ns
I _{RM}	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.7	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	9.1	-	А
E _{as}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		30	-	-	mJ



 V_o = 1.436 V; R_s = 0.0127 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values Fig. 6. Forward current as a function of forward voltage

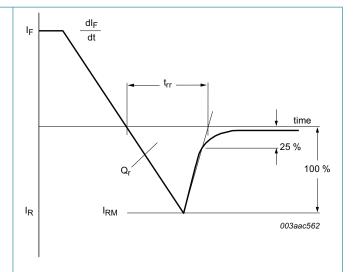
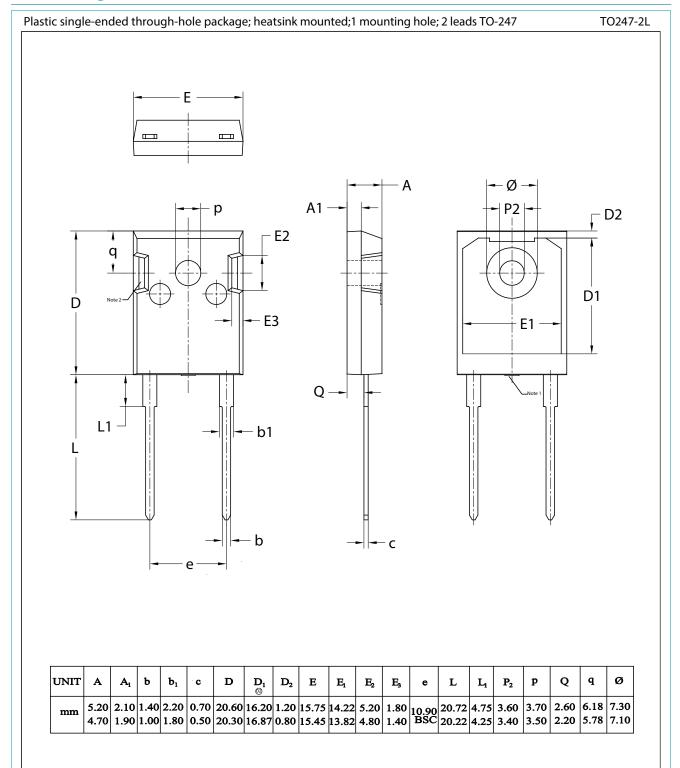


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Note:

- 1. Mold resin protrusion max 0.127mm.
- 2. Metal exposed with Sn plating.

BYC30MW-650PT2

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